OPA5816

Yellow LED Chip

GaAsP/GaP

1. Material

Substrate	GaP	(N Type)
Epitaxial Layer	GaAsP	(P/N Type)

2. Electrode

N(Cathode) Side Gold Alloy
P(Anode) Side Gold Alloy

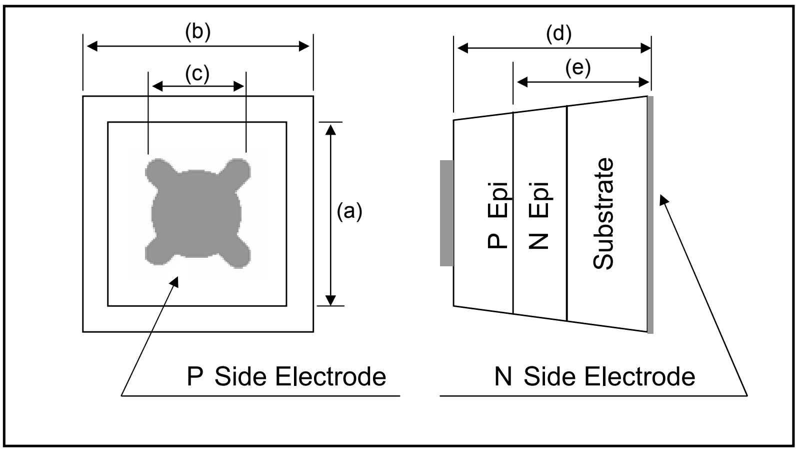
3. Electro-Optical Characteristics

Parameter	Symbol	Min	Typ	Max	Unit	Condition
Forward Voltage	$V_{F(1)}$		1.7		V	IF=1mA
	$V_{F(2)}$		2.15	2.3	V	IF=20mA
Reverse Voltage	V_R	8			V	IR=10uA
Brightness	Iv	140	200		mcd	IF=20mA
Wavelength	λ_d		588		nm	IF=20mA
	$\Delta\lambda$		40		nm	IF=20mA

※ Note : Brightness is measured by Sorter E/T system with bare chip.

4. Mechanical Data

(a) Emission Area	---------------------	10mil x 10mil
(b) Bottom Area	---------------------	11mil x 11mil
(c) Bonding Pad	---------------------	115um
(d) Chip Thickness	---------------------	11mil
(e) Junction Height	---------------------	10.6mil



AUK Corp.
Eoyang factory,513-5 Eoyang-dong, Iksan, 570-210, Kore
Tel. +82 63 839 1111 **Fax.** +82 63 835 8259
www.auk.co.kr